

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known	
			Application Number	10-766,205
			Filing Date	
			First Named Inventor	Shahid Rauf et al.
			Group Art Unit	
Sheet 1 of 1			Examiner Name	
			Attorney Docket Number	SC13121TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
gag	AA	4,957,834	09/18/1990	Matsuda <i>et al.</i>	
	AB	5,691,090	11/25/1997	Isao <i>et al.</i>	
gag	AC	6,524,755	02/25/2003	Jin <i>et al.</i>	

FOREIGN PATENT DOCUMENTS						
Examine Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
gag	AD	EP 0 668 539 A2	08/23/1995	Dove <i>et al.</i>		

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
gag	AE	Constantine <i>et al.</i> , "ICP Quartz Etch Uniformity Improvement for Phase Shift Mask Fabrication," <i>Part of the SPIE Conference on Photomask and X-Ray Mask Technology V</i> , Kawasaki, Japan, SPIE, Vol. 3412, April 1998, pp. 220-			/
	AF	Dahm <i>et al.</i> , "Quartz Etching for Phase Shifting Masks," <i>Microelectronic Engineering</i> , 1995, Vol. 27, pp. 263-266.			/
	AG	Wu <i>et al.</i> , "CF ₄ /O ₂ Plasma Simulation and Comparison with Quartz Etch Experiment," <i>Photomask and Next-Generation Lithography Mask Technology VIII</i> , Hiroichi Kawahira, Editor, <i>Proceedings of SPIE</i> , 2001, Vol. 4409, pp. 409-417.			/
gag	AH	Zeze <i>et al.</i> , "Reactive Ion Etching of Quartz and Pyrex for Microelectronic Applications," <i>Journal of Applied Physics</i> , October 2002, Vol. 92, No. 7, pp. 3624-3629.			/

Examiner Signature	George Goudreau	Date Considered	3-05'
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¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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